

Bariloche, Argentine Patagonia, February 25, 2013

The Department of Condensed Matter of the Physics Division of the Bariloche Atomic Center (National Atomic Energy Commission, Argentina), is seeking to incorporate researchers to work in the Optoelectronic Devices project of interest to the Department:

- *Modeling and design of optoelectronic devices based in III-V semiconductors*
The candidate must have a solid background in Solid State Physics, with special emphasis in low dimensional semiconductor systems. She/he must also have experience in calculation techniques of electron transport, electron-phonon, electron-photon and electron-electron scattering
- *Growth and characterization of III-V semiconductor structures by Molecular Beam Epitaxy (MBE)*
The candidate must have a solid background in experimental Solid State Physics. She/He must have experience in thin film and multilayer growth and structural characterization techniques.

The researcher will work in close collaboration with the experimental groups of Optoelectronics and Photonic Lab (<http://fisica.cab.cnea.gov.ar/pop/>), and Low Temperatures (<http://fisica.cab.cnea.gov.ar/bt>). They will have access to the semiconductor thin film grow equipment (MBE Riber Compact 21) and several microfabrication and characterization equipment available in the Centro Atómico Bariloche.

The candidates should be motivated to work independently as well as in close collaboration with the research groups in the Department. Postdoctoral experience is required.

The selected researchers will be endorsed for their presentation to the Scientific Research Career of the National Scientific and Technological Council (CONICET).

Candidates should send the following documents before March 18 to hernan@cab.cnea.gov.ar

- Curriculum vitae
- Work plan
- Two physicists who could be asked for references on the candidate.

All postulations will be evaluated by an ad-hoc commission and the results communicated on March 29.